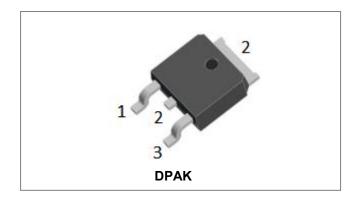


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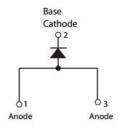
## **SDURD1030 ULTRAFAST RECTIFIER**



### **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### **Circuit Diagram**



### **Features**

- Ultra-Fast switching
- · High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Maximum Ratings:**

Characteristics	Symbol	Condition Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	300	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=100°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@10A, Pulse, T <sub>J</sub> = 25℃	1.06	1.3	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25℃	0.05	30	μA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125℃	0.007	1	mA
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =500mA, I <sub>R</sub> =1A,and I <sub>m</sub> =250mA	27	35	ns

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%

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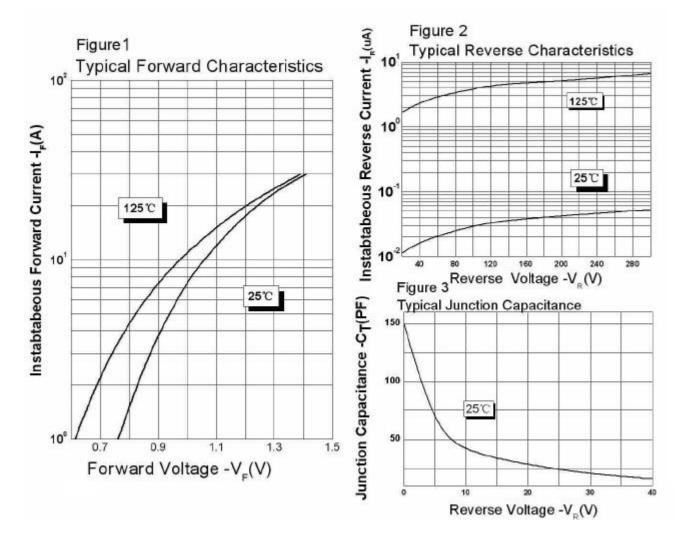




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	5.0	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

## **Ratings and Characteristics Curves**



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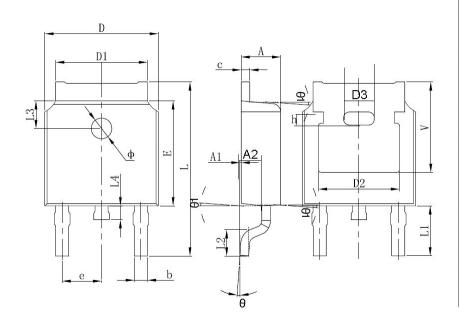


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### **Mechanical Dimensions DPAK**



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
Α	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
С	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35 REF.		0.211	REF.

### **Ordering Information**

Device	Package	Shipping	
SDURD1030	DPAK (Pb-Free)	2500pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

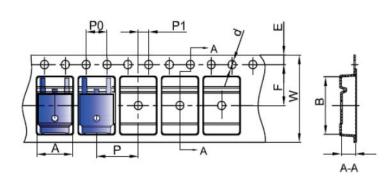
SDUR = Device Type
D = Package type
10 = Forward Current (10A)
30 = Reverse Voltage (300V)

SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

### **Carrier Tape Specification DPAK**



SYMBOL	Millimeters		
	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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### SDURD1030



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